

HD74HC1G08

2-input AND Gate

REJ03D0185-0500Z (Previous ADE-205-312C (Z)) Rev.5.00 Jan.27.2004

Description

The HD74HC1G08 is high speed CMOS two input AND gate using silicon gate CMOS process. With CMOS low power dissipation, it provides high-speed equivalent to LS-TTL series. The internal circuit of three stages construction with buffer provides wide noise margin and stable output.

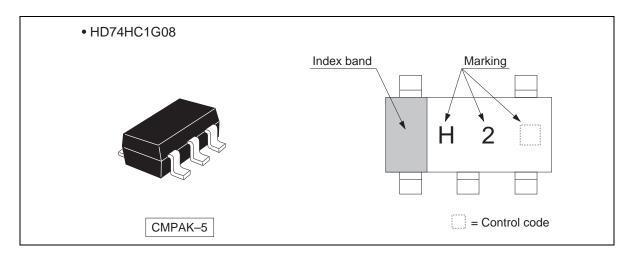
Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Electrical characteristics equivalent to the HD74HC08 Supply voltage range: 2 to 6 V
 Operating temperature range: -40 to +85°C
- $|I_{OH}| = I_{OL} = 2 \text{ mA (min)}$
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC1G08CME	CMPAK-5 pin	CMPAK-5V	CM	E (3,000 pcs/reel)

HD74HC1G08

Outline and Article Indication



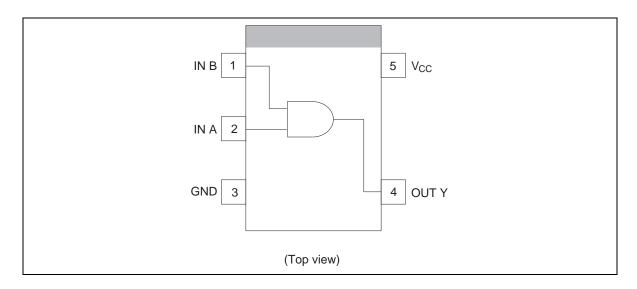
Function Table

Inputs

A	В	Output Y
L	L	L
Н	L	L
L	Н	L
Н	Н	Н

H : High level L : Low level

Pin Arrangement



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Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V _{CC}	–0.5 to 7.0	V	
Input voltage range *1	Vı	-0.5 to V _{CC} + 0.5	V	
Output voltage range *1, 2	Vo	-0.5 to V _{CC} + 0.5	V	Output : H or L
Input clamp current	I _{IK}	±20	mA	$V_I < 0$ or $V_I > V_{CC}$
Output clamp current	I _{OK}	±20	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	Io	±25	mA	$V_{O} = 0$ to V_{CC}
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±25	mA	
Maximum power dissipation at Ta = 25°C (in still air) *3	P _T	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Symbol	Min	Max	Unit	Test Conditions
Vcc	2	6	V	
Vı	0	V _{CC}	V	
Vo	0	V _{CC}	V	
l _{OL}	_	2.0	mA	$V_{CC} = 4.5 \text{ V}$
	_	2.6		$V_{CC} = 6.0 \text{ V}$
I _{OH}	_	-2.0	mA	V _{CC} = 4.5 V
	_	-2.6		$V_{CC} = 6.0 \text{ V}$
t _r , t _f	0	1000	ns	V _{CC} = 2.0 V
	0	500		$V_{CC} = 4.5 \text{ V}$
	0	400		$V_{CC} = 6.0 \text{ V}$
Та	-40	85	°C	
	V _{CC} V _I V _O I _{OL} I _{OH}	V _{CC} 2 V _I 0 V _O 0 I _{OL} — I _{OH} — t _r , t _f 0 0 0	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

Note: Unused or floating inputs must be held high or low.



HD74HC1G08

Electrical Characteristics

	V_{CC} $T_a = 25^{\circ}C$ $T_a = -40 \text{ to } 85$		10 to 85°C							
Item	Symbol	(V)	Min	Тур	Max	Min	Max	Unit	Test Con	ditions
Input voltage	V _{IH}	2.0	1.5	_	_	1.5	_	V		
		4.5	3.15	_	_	3.15	_	-		
		6.0	4.2	_	_	4.2	_	_		
	V _{IL}	2.0	_	_	0.5	_	0.5	=		
		4.5	_	_	1.35	_	1.35	_		
		6.0	_	_	1.8	_	1.8	_		
Output voltage	V _{OH}	2.0	1.9	2.0	_	1.9	_	V	V _{IN} =	$I_{OH} = -20 \mu A$
		4.5	4.4	4.5	_	4.4		_	V_{IH} or V_{IL}	
		6.0	5.9	6.0	_	5.9	_			
		4.5	4.18	4.31	_	4.13	_	_		$I_{OH} = -2 \text{ mA}$
		6.0	5.68	5.80	_	5.63	_			$I_{OH} = -2.6 \text{ mA}$
	V _{OL}	2.0	_	0.0	0.1	_	0.1	_		I _{OL} = 20 μA
		4.5	_	0.0	0.1	_	0.1	_		
		6.0	_	0.0	0.1	_	0.1	=		
		4.5	_	0.17	0.26	_	0.33	_		I _{OL} = 2 mA
		6.0	_	0.18	0.26	_	0.33	=		I _{OL} = 2.6 mA
Input current	I _{IN}	6.0	_	_	±0.1	_	±1.0	μΑ	$V_{IN} = V_{CC}$	or GND
Operating current	I _{CC}	6.0	_	_	1.0		10.0	μΑ	$V_{IN} = V_{CC}$ or GND	

Switching Characteristics

 $Ta = 25^{\circ}C$

			_					
Item	Symbol	Min	Тур	Max	Unit	Test Conditions		
Output rise / fall time	t _{TLH} t _{THL}	_	5	10	ns	Test circuit		
Propagation delay time	t _{PLH} t _{PHL}	_	7	15	ns	Test circuit		

 $C_L = 15 \text{ pF}, t_r = t_f = 6 \text{ ns}, V_{CC} = 5 \text{ V}$

		\mathbf{V}_{CC}	Ta = 25°C		Ta = -4	0 to 85°C			
Item	Symbol	(V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Output rise / fall time	t _{TLH}	2.0	_	50	125	_	155	ns	Test circuit
	t_{THL}	4.5	_	14	25	_	31	_	
		6.0	_	12	21	_	26	=	
Propagation delay time	t _{PLH}	2.0	_	48	100	_	125	ns	Test circuit
	t_{PHL}	4.5	_	12	20	_	25	=	
		6.0	_	9	17	_	21	=	
Input capacitance	C _{IN}	_	_	2.5	5	_	5	pF	
Equivalent capacitance	C _{PD}	_	_	10	_	_	_	pF	

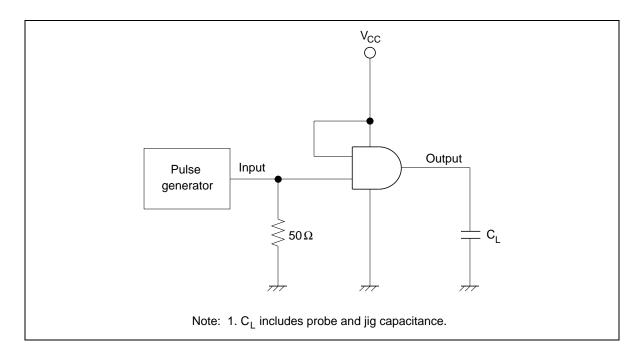
 $(C_L = 50 \text{ pF}, t_r = t_f = 6 \text{ ns})$

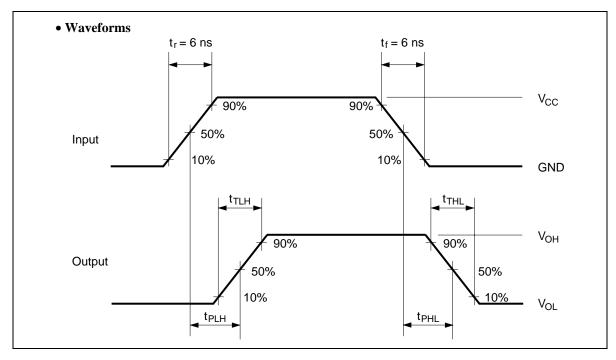
Note: C_{PD} is equivalent capacitance inside of the IC calculated from the operating current without load (see test circuit). The average operating current without load is calculated according to the expression

 I_{CC} (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

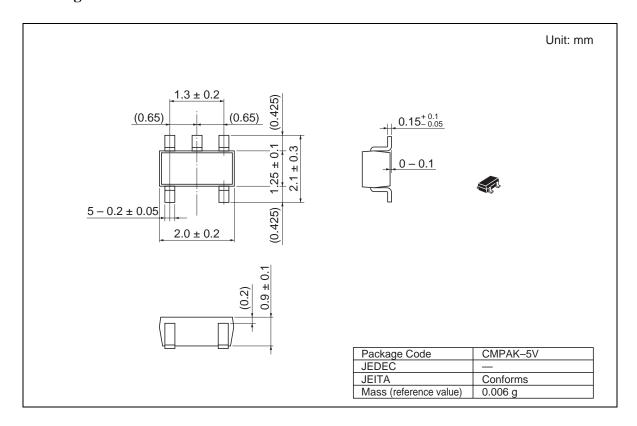


Test Circuit





Package Dimensions



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